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Docket No.: 503.38097CX1

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A semiconductor device comprising:  
a semiconductor substrate; and  
~~a semiconductor element which comprises:~~  
a first electrode provided on a front plane of said  
semiconductor substrate; and  
a second electrode provided on a rear plane of said  
semiconductor substrate;  
a first metallic member connected to said first  
electrode; and  
a second metallic member connected to said second  
electrode via a metallic layer containing precious metal; wherein  
~~said second electrode is connected to said second~~  
~~metallic member via a metallic layer containing precious metal, and~~  
~~said metallic layer is a composite metal layer comprised of a first~~  
~~precious metal layer provided at the front plane of said second electrode and a~~  
~~second precious metal layer adhered thereto by compression bonding provided at~~  
~~the front plane of said second metallic member.~~  
  
Wherein said metallic layer is a composite metal layer comprised of a  
first precious metal layer metallicity bonded to said second electrode and a second  
precious metal layer metallicity bonded to said second metallic member, said first

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precious metal layer being adhered to said second precious metal layer by compression bonding.

2. (Currently Amended) A semiconductor device comprising:

a semiconductor ~~chip, chip,~~ and

an electrode provided on said semiconductor chip, and

a metallic member connected to ~~a chip~~ said electrode,

wherein:

~~said chip electrode is composed of any~~ comprises one of an Al film and an Al alloy film;

a ~~bonding front plane of said metallic member is composed of~~ provided with a plated precious metal film;

~~said chip electrode is~~ metallically bonded to said plated precious metal film provided on ~~bonded-metallically-to-said~~ metallic member via Au bumps, said Au bumps being adhered to said plated precious metal film by compression bonding; and

~~at least 80% of an area of a respective Au/Al bonding region is~~ at least 80% of contacting a area of said Au bumps, said bonding region being made of an Au/Al alloy layer in the thickness direction.

3. (Cancelled)

4. (Previously Presented) A semiconductor device according to claim 1,

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wherein a surface part of said first metallic member for connecting to outer wirings and a surface part of said second metallic member are substantially positioned in a same plane.

5. (Previously Presented) A semiconductor device according to claim 1, wherein said first electrode and said first metallic member are connected through plural protruding electrodes.

6. (Currently Amended) A semiconductor device according to claim 1, wherein said metallic layer is made of metal alloy layer having a solid phase temperature of more than 400° C and containing said precious metal as a main component.

7. (Previously Presented) A semiconductor device according to claim 1, wherein at least one of a bump electrode made of said precious metal, a ball shaped electrode, a Ag particle mixed with resin, a Ag member having a plate shape, a sheet shape or a mesh shape or a Ag member of a plate shape or a sheet shape being convex/concave or having an air gap part is provided between a precious metallic layer positioned on said second electrode and a precious metallic layer positioned on said second metallic member.

8. (Currently Amended) A semiconductor device according to claim 1, wherein said first metallic member is connected to plural outer wirings extended from a part having a connecting part of said first electrode.